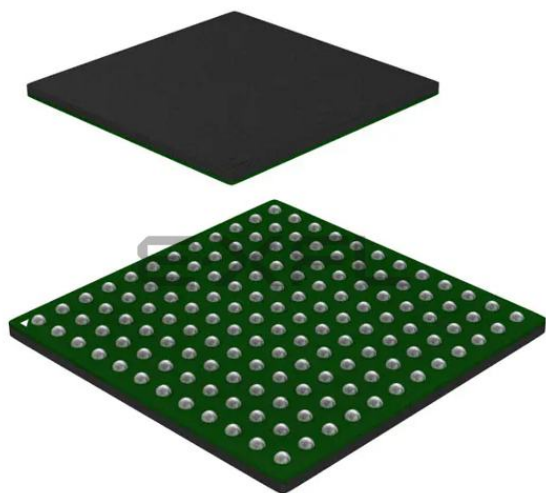




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, MMC/SDIO, QSPI, SAI, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-UFBGA
Supplier Device Package	144-UFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f413zhj6

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3.11 Quad-SPI memory interface (QUAD-SPI)

All devices embed a Quad-SPI memory interface, which is a specialized communication interface targeting single, dual or quad-SPI Flash memories. It can work in direct mode through registers, external Flash status register polling mode and memory mapped mode. Up to 256 Mbyte of external Flash memory are mapped. They can be accessed in 8, 16 or 32-bit mode. Code execution is also supported. The opcode and the frame format are fully programmable. Communication can be performed either in single data rate or dual data rate.

3.12 Nested vectored interrupt controller (NVIC)

The devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 102 maskable interrupt channels plus the 16 interrupt lines of the Cortex®-M4 with FPU.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

3.13 External interrupt/event controller (EXTI)

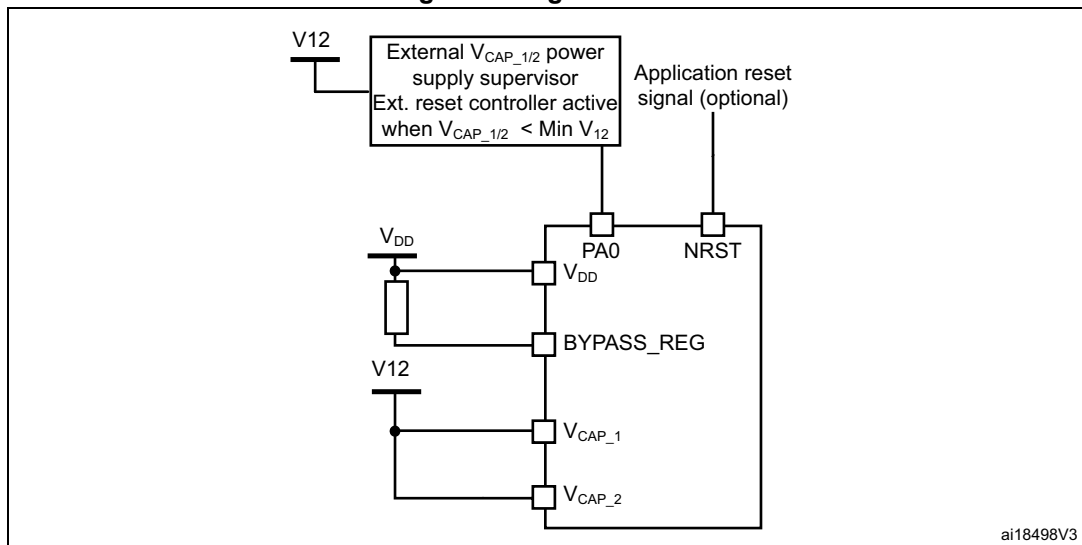
The external interrupt/event controller consists of 24 edge-detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 114 GPIOs can be connected to the 16 external interrupt lines.

3.14 Clocks and startup

On reset the 16 MHz internal RC oscillator is selected as the default CPU clock. The 16 MHz internal RC oscillator is factory-trimmed to offer 1% accuracy at 25 °C. The application can then select as system clock either the RC oscillator or an external 4-26 MHz clock source. This clock can be monitored for failure. If a failure is detected, the system automatically switches back to the internal RC oscillator and a software interrupt is generated (if enabled). This clock source is input to a PLL thus allowing to increase the frequency up to 100 MHz. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example if an indirectly used external oscillator fails).

Several prescalers allow the configuration of the three AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the three AHB

Figure 8. Regulator OFF



The following conditions must be respected:

- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is faster than the time for V_{DD} to reach 1.7 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V_{12} minimum value and until V_{DD} reaches 1.7 V (see [Figure 9](#)).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.7 V, then PA0 could be asserted low externally (see [Figure 10](#)).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.7 V, then a reset must be asserted on PA0 pin.

Note: The minimum value of V_{12} depends on the maximum frequency targeted in the application.

Additional 32-bit registers contain the programmable alarm subseconds, seconds, minutes, hours, day, and date.

The RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or from the VBAT pin.

3.20 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

To further reduce the power consumption, the Flash memory can be switched off before entering in Sleep mode. Note that this requires a code execution from the RAM.

- **Stop mode**

The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm/ wakeup/ tamper/ time stamp events).

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on one of the WKUP pins, or an RTC alarm/ wakeup/ tamper/time stamp event occurs.

Standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

3.21 V_{BAT} operation

The VBAT pin allows to power the device V_{BAT} domain from an external battery, an external super-capacitor, or from V_{DD} when no external battery and an external super-capacitor are present.

V_{BAT} operation is activated when V_{DD} is not present.

The VBAT pin supplies the RTC and the backup registers.

Note: When the microcontroller is supplied from V_{BAT} , external interrupts and RTC alarm/events do not exit it from V_{BAT} operation. When PDR_ON pin is not connected to V_{DD} (internal Reset OFF), the V_{BAT} functionality is no more available and VBAT pin should be connected to V_{DD} .

3.25 Serial peripheral interface (SPI)

The devices feature five SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1, SPI4 and SPI5 can communicate at up to 50 Mbit/s, SPI2 and SPI3 can communicate at up to 25 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes. All SPIs can be served by the DMA controller.

The SPI interfaces can be configured to operate in TI mode for communications in master mode and slave mode.

3.26 Inter-integrated sound (I²S)

Five standard I²S interfaces (multiplexed with SPI1 to SPI5) are available. They can be operated in master or slave mode, in simplex communication mode, and full duplex mode for I2S2 and I2S3. All I²S interfaces can be configured to operate with a 16-/32-bit resolution as an input or output channel. I2Sx audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I²S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

All I²Sx interfaces can be served by the DMA controller.

3.27 Serial Audio interface (SAI1)

The serial audio interface (SAI1) is based on two independent audio sub-blocks which can operate as transmitter or receiver with their FIFO. Many audio protocols are supported by each block: I2S standards, LSB or MSB-justified, PCM/DSP, TDM, AC'97 and SPDIF output, supporting audio sampling frequencies from 8 kHz up to 192 kHz. Both sub-blocks can be configured in master or in slave mode.

In master mode, the master clock can be output to the external DAC/CODEC at 256 times of the sampling frequency.

The two sub-blocks can be configured in synchronous mode when full-duplex mode is required.

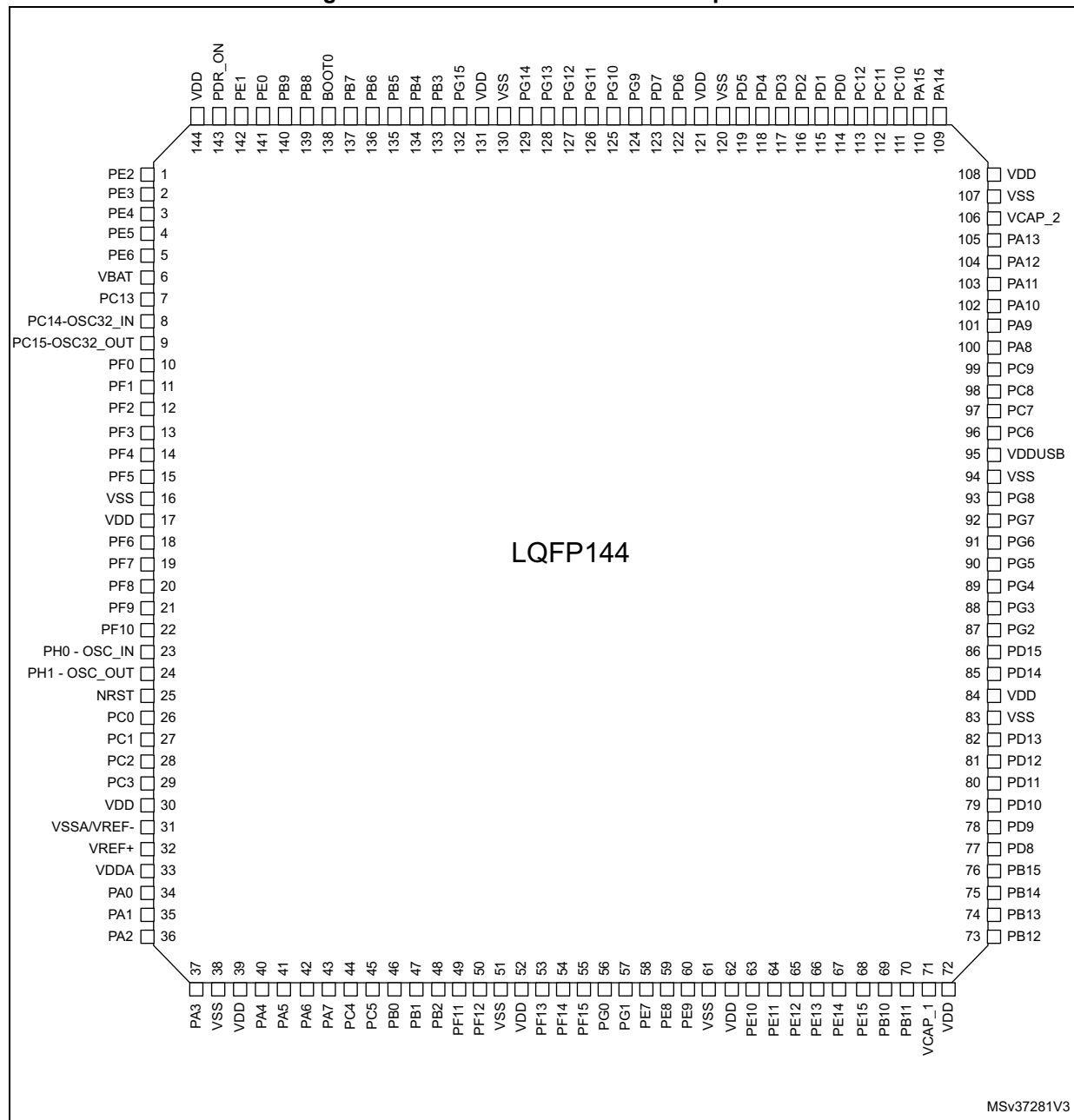
SAI1 can be served by the DMA controller.

3.28 Audio PLL (PLLI2S)

The devices feature an additional dedicated PLL for audio I²S and SAI applications. It allows to achieve error-free I²S sampling clock accuracy without compromising on the CPU performance, while using USB peripherals.

Different sources can be selected for the I2S master clock of the APB1 and the I2S master clock of the APB2. This gives the flexibility to work with two different audio sampling frequencies. The different possible sources are the main PLL, the PLLI2S, HSE or HSI clocks or an external clock provided through a pin (external PLL or CODEC output)

Figure 15. STM32F413xG/H LQFP144 pinout



1. The above figure shows the package top view.

Table 10. STM32F413xG/H pin definition (continued)

Pin Number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP81	LQFP100	UFBGA100	UFBGA144	LQFP144						
-	-	-	-	-	D4	12	PF2	I/O	FT	-	I2C2_SMB, FSMC_A2, EVENTOUT	-
-	-	-	-	-	E2	13	PF3	I/O	FT	-	TIM5_CH1, FSMC_A3, EVENTOUT	-
-	-	-	-	-	E3	14	PF4	I/O	FT	-	TIM5_CH2, FSMC_A4, EVENTOUT	-
-	-	-	-	-	E4	15	PF5	I/O	FT	-	TIM5_CH3, FSMC_A5, EVENTOUT	-
-	-	D8	10	F2	D2	16	VSS	S	-	-	-	-
-	-	E8	11	G2	D3	17	VDD	S	-	-	-	-
-	-	-	-	-	F3	18	PF6	I/O	FT	-	TRACED0, TIM10_CH1, SAI1_SD_B, UART7_Rx, QUADSPI_BK1_IO3, EVENTOUT	-
-	-	-	-	-	F2	19	PF7	I/O	FT	-	TRACED1, TIM11_CH1, SAI1_MCLK_B, UART7_Tx, QUADSPI_BK1_IO2, EVENTOUT	-
-	-	-	-	-	G3	20	PF8	I/O	FT	-	SAI1_SCK_B, UART8_RX, TIM13_CH1, QUADSPI_BK1_IO0, EVENTOUT	-
-	-	-	-	-	G2	21	PF9	I/O	FT	-	SAI1_FS_B, UART8_TX, TIM14_CH1, QUADSPI_BK1_IO1, EVENTOUT	-
-	-	-	-	-	G1	22	PF10	I/O	FT	-	TIM1_ETR, TIM5_CH4, EVENTOUT	-
5	5	E9	12	F1	D1	23	PH0 - OSC_IN	I/O	FT	⁽⁶⁾	EVENTOUT	OSC_IN
6	6	F9	13	G1	E1	24	PH1 - OSC_OUT	I/O	FT	⁽⁶⁾	EVENTOUT	OSC_OUT
7	7	G9	14	H2	F1	25	NRST	I/O	RST	-	-	NRST
-	8	F8	15	H1	H1	26	PC0	I/O	FT	-	LPTIM1_IN1, DFSDM2_CKIN4, SAI1_MCLK_B, EVENTOUT	ADC1_IN10, WKUP2

Table 10. STM32F413xG/H pin definition (continued)

Pin Number							Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP81	LQFP100	UFBGA100	UFBGA144	LQFP144						
41	57	A6	91	C5	B6	135	PB5	I/O	FT	-	LPTIM1_IN1, TIM3_CH2, I2C1_SMBA, SPI1_MOSI/I2S1_SD, SPI3_MOSI/I2S3_SD, CAN2_RX, SAI1_FS_A, UART5_RX, SDIO_D3, EVENTOUT	-
42	58	B6	92	B5	C6	136	PB6	I/O	FT	-	LPTIM1_ETR, TIM4_CH1, I2C1_SCL, DFSDM2_CKIN7, USART1_TX, CAN2_TX, QUADSPI_BK1_NCS, UART5_TX, SDIO_D0, EVENTOUT	-
43	59	B7	93	B4	D6	137	PB7	I/O	FT	-	LPTIM1_IN2, TIM4_CH2, I2C1_SDA, DFSDM2_DATIN7, USART1_RX, FSMC_NL, EVENTOUT	-
44	60	A7	94	A4	D5	138	BOOT0	I	B	-	-	VPP
45	61	C6	95	A3	C5	139	PB8	I/O	FT	-	LPTIM1_OUT, TIM4_CH3, TIM10_CH1, I2C1_SCL, SPI5_MOSI/I2S5_SD, DFSDM2_CKIN1, CAN1_RX, I2C3_SDA, UART5_RX, SDIO_D4, EVENTOUT	-
46	62	D6	96	B3	B5	140	PB9	I/O	FT	-	TIM4_CH4, TIM11_CH1, I2C1_SDA, SPI2_NSS/I2S2_WS, DFSDM2_DATIN1, CAN1_TX, I2C2_SDA, UART5_TX, SDIO_D5, EVENTOUT	-
-	-	NC	97	C3	A5	141	PE0	I/O	FT	(2)	TIM4_ETR, DFSDM2_CKIN4, UART8_Rx, FSMC_NBL0, EVENTOUT	-
-	-	NC	98	A2	A4	142	PE1	I/O	FT	(2)	DFSDM2_DATIN4, UART8_Tx, FSMC_NBL1, EVENTOUT	-
47	63	A8	99	D3	E6	-	VSS	S	-	-	-	-

Table 12. STM32F413xG/H alternate functions (continued)

Port	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
	SYS_AF	TIM1/2/ LPTIM1	TIM3/4/5	DFSDM2/ TIM8/9/10/11	I2C1/2/3/ I2CFMP1	SPI1/I2S1/ SPI2/I2S2/ SPI3/I2S3/ SPI4/I2S4	SPI2/I2S2/ SPI3/I2S3/ SPI4/I2S4/ SPI5/I2S5/ DFSDM1/2	SPI3/I2S3/ SAI1/ DFSDM2/ USART1/ USART2/ USART3	DFSDM1/ USART3/4/ 5/6/7/8/ CAN1	I2C2/I2C3/ I2CFMP1/ CAN1/2/ TIM12/13/14/ QUADSPI	SAI1/ DFSDM1/ DFSDM2/ QUADSPI/ FSMC /OTG1_FS	UART4/ UART5/ UART9/ UART10 /CAN3	FSMC /SDIO	-	RNG	SYS_AF
Port B	PB0	-	TIM1_CH2N	TIM3_CH3	TIM8_CH2N	-	-	SPI5_SCK/I2S5_CK	-	-	-	-	-	-	-	EVENT OUT
	PB1	-	TIM1_CH3N	TIM3_CH4	TIM8_CH3N	-	-	SPI5_NSS/I2S5_WS	-	DFSDM1_DATIN0	QUADSPI_C_LK	-	-	-	-	EVENT OUT
	PB2	-	LPTIM1_OUT	-	-	-	-	DFSDM1_CKIN0	-	-	QUADSPI_C_LK	-	-	-	-	EVENT OUT
	PB3	JTDO-SWO	TIM2_CH2	-	-	I2CFMP1_SDA	SPI1_SCK/I2S1_CK	SPI3_SCK/I2S3_CK	USART1_RX	UART7_RX	I2C2_SDA	SAI1_SD_A	CAN3_RX	-	-	EVENT OUT
	PB4	JTRST	-	TIM3_CH1	-	-	SPI1_MISO	SPI3_MISO	I2S3ext_SD	UART7_TX	I2C3_SDA	SAI1_SCK_A	CAN3_TX	SDIO_D0	-	EVENT OUT
	PB5	-	LPTIM1_IN1	TIM3_CH2	-	I2C1_SMBA	SPI1_MOS/I2S1_SD	SPI3_MOS/I2S3_SD	-	-	CAN2_RX	SAI1_FS_A	UART5_RX	SDIO_D3	-	EVENT OUT
	PB6	-	LPTIM1_ETR	TIM4_CH1	-	I2C1_SCL	-	DFSDM2_CKIN7	USART1_TX	-	CAN2_TX	QUADSPI_BK1_NCS	UART5_TX	SDIO_D0	-	EVENT OUT
	PB7	-	LPTIM1_IN2	TIM4_CH2	-	I2C1_SDA	-	DFSDM2_DATIN7	USART1_RX	-	-	-	FSMC_NL	-	-	EVENT OUT
	PB8	-	LPTIM1_OUT	TIM4_CH3	TIM10_CH1	I2C1_SCL	-	SPI5_MOS/I2S5_SD	DFSDM2_CKIN1	CAN1_RX	I2C3_SDA	-	UART5_RX	SDIO_D4	-	EVENT OUT
	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS/I2S2_WS	DFSDM2_DATIN1	-	CAN1_TX	I2C2_SDA	-	UART5_TX	SDIO_D5	-	EVENT OUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK/I2S2_CK	I2S3_MCK	USART3_TX	-	I2CFMP4_SCL	DFSDM2_CKOUT	-	SDIO_D7	-	EVENT OUT
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	I2S2_CKIN	-	USART3_RX	-	-	-	-	-	-	EVENT OUT
	PB12	-	TIM1_BKIN	-	-	I2C2_SMBA	SPI2_NSS/I2S2_WS	SPI4_NSS/I2S4_WS	SPI3_SCK/I2S3_CK	USART3_CK	CAN2_RX	DFSDM1_DATIN1	UART5_RX	FSMC_D13/FSMC_DA13	-	EVENT OUT
	PB13	-	TIM1_CH1N	-	-	I2CFMP1_SMBA	SPI2_SCK/I2S2_CK	SPI4_SCK/I2S4_CK	-	USART3_CTS	CAN2_TX	DFSDM1_CKIN1	UART5_TX	-	-	EVENT OUT
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	I2CFMP1_SDA	SPI2_MISO	I2S2ext_SD	USART3_RTS	DFSDM1_DATIN2	TIM12_CH1	FSMC_D0/FSMC_DA0	-	SDIO_D6	-	EVENT OUT
	PB15	RTC_REFIN	TIM1_CH3N	-	TIM8_CH3N	I2CFMP1_SCL	SPI2_MOS/I2S2_SD	-	-	DFSDM1_CKIN2	TIM12_CH2	-	-	SDIO_CK	-	EVENT OUT

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A .

Table 21. Operating conditions at power-up / power-down (regulator OFF)⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	$\mu s/V$
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below 1.08 V.

Note: This feature is only available for UFBGA100 and UFBGA144 packages.

6.3.5 Embedded reset and power control block characteristics

The parameters given in [Table 22](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage @ 3.3V.

Table 22. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	
		PLS[2:0]=101 (falling edge)	2.65	2.84	3.02	
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	
$V_{PVDhyst}^{(2)}$	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60 ⁽¹⁾	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	

Table 25. Typical and maximum current consumption in run mode, code with data processing (ART accelerator enabled except prefetch) running from Flash memory- $V_{DD} = 1.7\text{ V}$

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾					Unit
				T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	T _A = 125 °C		
I _{DD}	Supply current in Run mode	External clock, PLL ON, all peripherals enabled ⁽²⁾⁽³⁾	100	30.2	32.03	32.71	34.69	38.46	mA	
			84	24.3	25.77	26.58	28.47	32.16		
			64	16.8	17.80	18.66	20.53	23.85		
			50	13.2	14.05	15.12	16.85	20.27		
			25	7.1	7.62	8.92	10.81	14.11		
			20	6.1	6.69	7.95	9.72	13.09		
		HSI, PLL OFF, all peripherals enabled ⁽²⁾	16	4.4	4.99	6.28	8.18	11.45		
			1	0.9	1.50	2.88	4.58	8.00		
		External clock, PLL ON ⁽⁴⁾ all peripherals disabled ⁽²⁾	100	12.6	13.46	14.75	16.68	20.54		
			84	10.2	10.90	12.25	14.10	17.84		
			64	7.2	7.70	8.95	10.81	14.14		
			50	5.7	6.26	7.56	9.26	12.72		
			25	3.2	3.77	5.11	6.82	10.26		
			20	2.9	3.41	4.79	6.49	9.92		
		HSI, PLL OFF, all peripherals disabled ⁽²⁾	16	2.1	2.63	3.91	5.80	9.06		
			1	0.8	1.34	2.72	4.42	7.86		

1. Guaranteed by characterization results..

2. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).

3. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

4. Refer to [Table 47](#) and RM0383 for the possible PLL VCO setting

6.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 55](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 54. EMS characteristics for LQFP144 package

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP144 $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 100\text{ MHz}$, conforms to IEC 61000-4-2	1B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP144 $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 100\text{ MHz}$, conforms to IEC 61000-4-4	3B

When the application is exposed to a noisy environment, it is recommended to avoid pin exposition to disturbances. The pins showing a middle range robustness are: PA0, PA1, PA2, on LQFP144 packages and PDR_ON on WLCSP81.

As a consequence, it is recommended to add a serial resistor (1 k Ω maximum) located as close as possible to the MCU to the pins exposed to noise (connected to tracks longer than 50 mm on PCB).

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Table 56. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	$T_A = +25\text{ }^{\circ}\text{C}$ conforming to JESD22-A114	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	$T_A = +25\text{ }^{\circ}\text{C}$ conforming to ANSI/ESD STM5.3.1, UFBGA144, UFBGA100, LQFP144, LQFP100, WLCSP81, LQFP64	3	250	
		$T_A = +25\text{ }^{\circ}\text{C}$ conforming to ANSI/ESD STM5.3.1, UFQFPN48	4	500	

1. Guaranteed by characterization results.

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 57. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +125\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

6.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

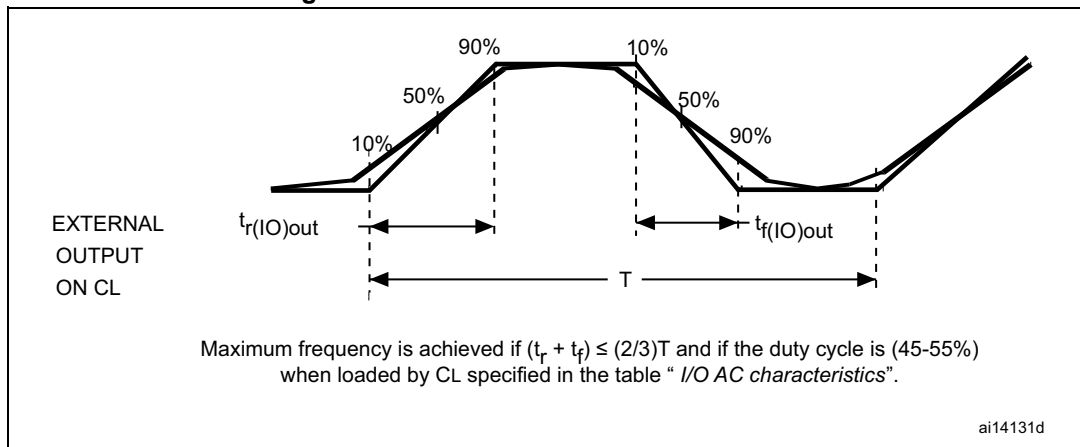
The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in [Table 58](#).

1. Guaranteed by characterization results.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in [Figure 36](#).
4. For maximum frequencies above 50 MHz and $V_{DD} > 2.4$ V, the compensation cell should be used.

Figure 36. I/O AC characteristics definition



6.3.17 NRST pin characteristics

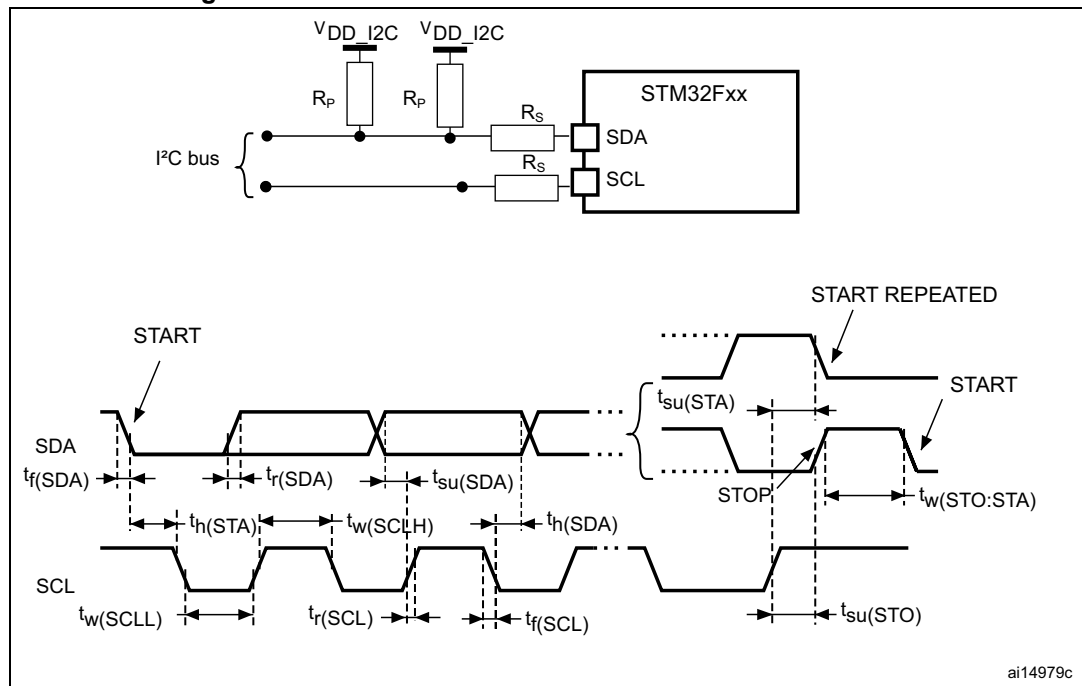
The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 59](#)).

Unless otherwise specified, the parameters given in [Table 62](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#). Refer to [Table 59: I/O static characteristics](#) for the values of V_{IH} and V_{IL} for NRST pin.

Table 62. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor ⁽¹⁾	$V_{IN} = V_{SS}$	30	40	50	k Ω
$V_{F(NRST)}^{(2)}$	NRST Input filtered pulse	-	-	-	100	ns
$V_{NF(NRST)}^{(2)}$	NRST Input not filtered pulse	$V_{DD} > 2.7$ V	300	-	-	ns
T_{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	-	μ s

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).
2. Guaranteed by design.

Figure 38. I²C bus AC waveforms and measurement circuit

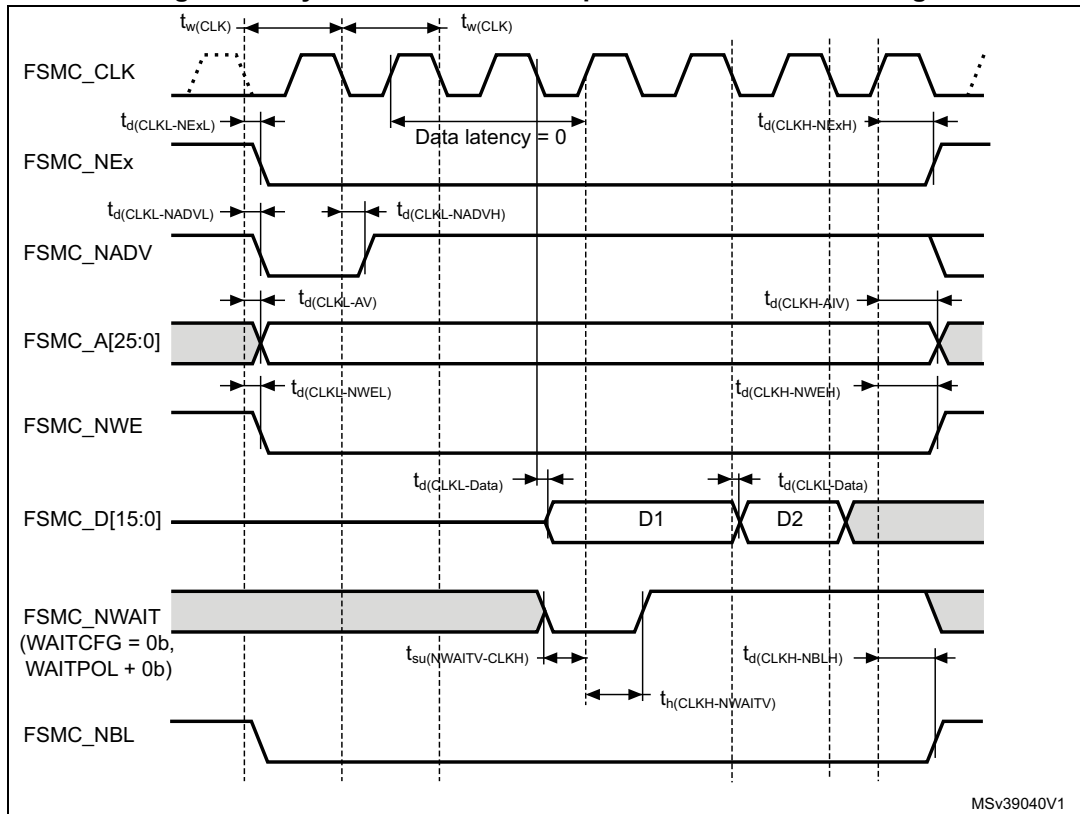
1. R_S = series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I2C bus power supply.

Table 65. SCL frequency ($f_{PCLK1} = 50$ MHz, $V_{DD} = V_{DD_I2C} = 3.3$ V)⁽¹⁾⁽²⁾

f_{SCL} (kHz)	I2C_CCR value
	$R_P = 4.7$ k Ω
400	0x8019
300	0x8021
200	0x8032
100	0x0096
50	0x012C
20	0x02EE

1. R_P = External pull-up resistance, f_{SCL} = I2C speed
2. For speeds around 200 kHz, the tolerance on the achieved speed is of $\pm 5\%$. For other speed ranges, the tolerance on the achieved speed is $\pm 2\%$. These variations depend on the accuracy of the external components used to design the application.

Figure 60. Synchronous non-multiplexed PSRAM write timings

Table 99. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_w(\text{CLK})$	FSMC_CLK period	$2 * T_{\text{HCLK}} - 0.5$	-	ns
$t_d(\text{CLKL-NExL})$	FSMC_CLK low to FSMC_NEx low ($x=0..2$)	-	2	
$t_d(\text{CLKH-NExH})$	FSMC_CLK high to FSMC_NEx high ($x=0..2$)	$T_{\text{HCLK}} + 0.5$	-	
$t_d(\text{CLKL-NADVL})$	FSMC_CLK low to FSMC_NADV low	-	0.5	
$t_d(\text{CLKL-NADVH})$	FSMC_CLK low to FSMC_NADV high	0	-	
$t_d(\text{CLKL-AV})$	FSMC_CLK low to FSMC_Ax valid ($x=16..25$)	-	2.5	
$t_d(\text{CLKH-AIV})$	FSMC_CLK high to FSMC_Ax invalid ($x=16..25$)	T_{HCLK}	-	
$t_d(\text{CLKL-NWEL})$	FSMC_CLK low to FSMC_NWE low	-	1.5	
$t_d(\text{CLKH-NWEH})$	FSMC_CLK high to FSMC_NWE high	$T_{\text{HCLK}} + 1$	-	
$t_d(\text{CLKL-Data})$	FSMC_D[15:0] valid data after FSMC_CLK low	-	4	
$t_d(\text{CLKL-NBL})$	FSMC_CLK low to FSMC_NBL low	-	2	
$t_d(\text{CLKH-NBLH})$	FSMC_CLK high to FSMC_NBL high	$T_{\text{HCLK}} + 1$	-	
$t_{\text{su}}(\text{NWAIT-CLKH})$	FSMC_NWAIT valid before FSMC_CLK high	2	-	
$t_h(\text{CLKH-NWAIT})$	FSMC_NWAIT valid after FSMC_CLK high	3.5	-	

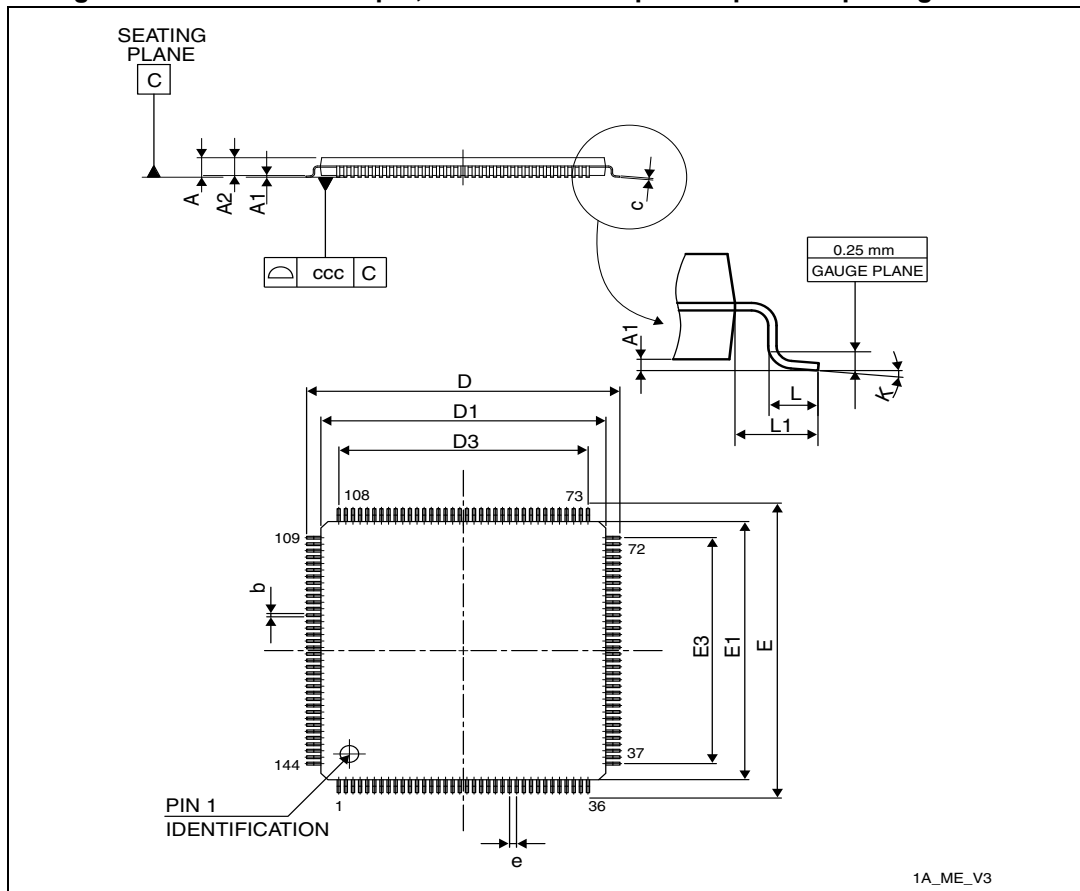
1. $C_L = 30 \text{ pF}$.

2. Guaranteed by characterization results.

[illegible]

7.5 LQFP144 package information

Figure 75. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 109. UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 79. UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package recommended footprint

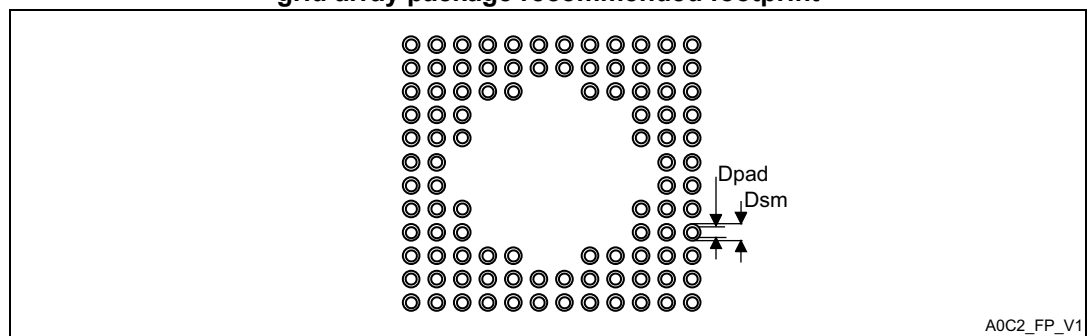


Table 110. UFBGA100 recommended PCB design rules (0.5 mm pitch BGA)

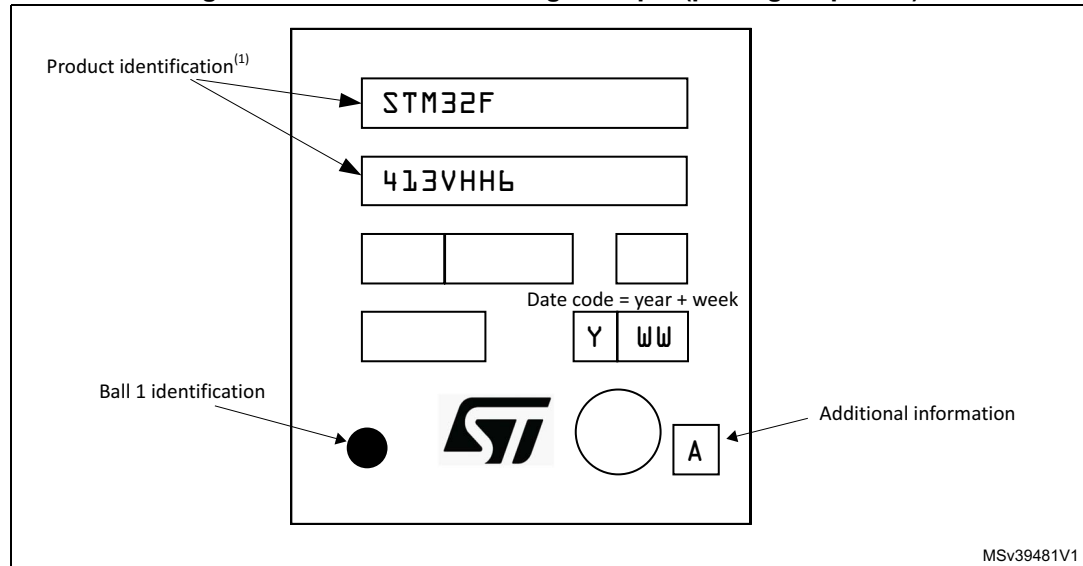
Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm

Device marking for UFBGA100

The following figure gives an example of topside marking and ball 1 position identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 80. UFBGA100 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.